

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1129	defects same silicon same copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 12:26
S2	28	electrolyte and bath and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:00
S3	99	d-defects	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:35
S4	62	copper and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:36
S5	2	(electro or electrolyte) and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 08:36
S6	1	("5783495").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/02 08:37
S7	8	("5980720").URPN.	USPAT	OR	ON	2005/03/02 08:39
S8	32919	(slot or slots) and copper	USPAT	OR	ON	2005/03/02 08:43
S9	0	S3 and S8	USPAT	OR	ON	2005/03/02 08:41
S10	1121	copper adj bath	USPAT	OR	ON	2005/03/02 08:42
S11	818	(wafer or substrate) and S10	USPAT	OR	ON	2005/03/02 08:42
S12	47	(slot or slots) and S11	USPAT	OR	ON	2005/03/02 08:43
S13	29	("3716462").URPN.	USPAT	OR	ON	2005/03/02 09:34
S14	4108	kim.in. and copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 10:48

S15	23	decoration and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 10:53
S16	1740	(438/14).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 10:54
S17	22	(438/441).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 12:23
S18	1412	(438/687).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/02 12:26
S19	232	(electrolyte or electrolytic or electrodeless) and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 12:27

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NEWS 6 DEC 01 LISA now available on STN
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NEWS 8 DEC 15 MEDLINE update schedule for December 2004
NEWS 9 DEC 17 ELCOM reloaded; updating to resume; current-awareness
 alerts (SDIs) affected
NEWS 10 DEC 17 COMPUAB reloaded; updating to resume; current-awareness
 alerts (SDIs) affected
NEWS 11 DEC 17 SOLIDSTATE reloaded; updating to resume; current-awareness
 alerts (SDIs) affected
NEWS 12 DEC 17 CERAB reloaded; updating to resume; current-awareness
 alerts (SDIs) affected
NEWS 13 DEC 17 THREE NEW FIELDS ADDED TO IFIPAT/IFIUDB/IFICDB
NEWS 14 DEC 30 EPFULL: New patent full text database to be available on STN
NEWS 15 DEC 30 CAPLUS - PATENT COVERAGE EXPANDED
NEWS 16 JAN 03 No connect-hour charges in EPFULL during January and
 February 2005
NEWS 17 FEB 25 CA/CAPLUS - Russian Agency for Patents and Trademarks
 (ROSPATENT) added to list of core patent offices covered
NEWS 18 FEB 10 STN Patent Forums to be held in March 2005
NEWS 19 FEB 16 STN User Update to be held in conjunction with the 229th ACS
 National Meeting on March 13, 2005
NEWS 20 FEB 28 PATDPAFULL - New display fields provide for legal status
 data from INPADOC
NEWS 21 FEB 28 BABS - Current-awareness alerts (SDIs) available
NEWS 22 FEB 28 MEDLINE/LMEDLINE reloaded

NEWS EXPRESS JANUARY 10 CURRENT WINDOWS VERSION IS V7.01a, CURRENT
 MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP),
 AND CURRENT DISCOVER FILE IS DATED 10 JANUARY 2005

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FILE 'HOME' ENTERED AT 08:26:23 ON 02 MAR 2005

=> file inspec

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST 0.21 0.21

FILE 'INSPEC' ENTERED AT 08:26:34 ON 02 MAR 2005
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FILE LAST UPDATED: 28 FEB 2005 <20050228/UP>
FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
THE BASIC INDEX >>>

=> s copper

L1 142605 COPPER

=> s silicon

L2 327234 SILICON

=> s defects

L3 116900 DEFECTS

=> s slots

L4 8159 SLOTS

=> s 11 and 12 and 13 and 14

L5 0 L1 AND L2 AND L3 AND L4

=> s copper bath

142605 COPPER

12284 BATH

L6 47 COPPER BATH

(COPPER (W) BATH)

=> s 13 and 16

L7 0 L3 AND L6

=> s analyzing defects

50370 ANALYZING

116900 DEFECTS

L8 8 ANALYZING DEFECTS

(ANALYZING (W) DEFECTS)

=> d 18 1-8

L8 ANSWER 1 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	References
AN 2004:8284130	INSPEC DN B2005-03-2550G-041
TI	Simulation of photoresist thermal flow process with viscous flow model.
AU	Won-Young Chung; Tai-Kyung Kim; Yero Lee (Semicond. R&D Center, Samsung Electron., Gyeonggi-Do, South Korea); Jin-Young Yoon; Hyun-Woo Kim; Young-Kwan Park; Jeong-Taek Kong
SO	Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers) (Sept. 2004) vol.43, no.9A, p.6020-5. 13 refs. Published by: Japan Soc. Appl. Phys
	CODEN: JAPNDE ISSN: 0021-4922
	SICI: 0021-4922(200409)43:9AL.6020:SPTF;1-I
DT	Journal
TC	Practical; Theoretical; Experimental
CY	Japan

LA English

L8 ANSWER 2 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Link References
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AN 2004:8128784 INSPEC DN B2004-11-2550G-163
 TI Simulation technique for the PR flow process using a new viscous flow model [photoresist].
 AU Won-Young Chung; Tai-Kyung Kim; Jin-Young Yoon; Hyun-Woo Kim; Young-Kwan Park; Jeong-Taek Kong (Semicond. R&D Center, Samsung Electron. Co. Ltd., Gyeonggi-Do, South Korea)
 SO Proceedings of the SPIE - The International Society for Optical Engineering (2004) vol.5376, no.1, p.975-82. 11 refs.
 Published by: SPIE-Int. Soc. Opt. Eng
 Price: CCCC 0277-786X/04/\$15.00
 CODEN: PSISDG ISSN: 0277-786X
 SICI: 0277-786X(2004)5376:1L.975:STFP;1-R
 Conference: Advances in Resist Technology and Processing XXI. Santa Clara, CA, USA, 23-24 Feb 2004
 DT Conference Article; Journal
 TC Practical; Theoretical; Experimental
 CY United States
 LA English

L8 ANSWER 3 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Link References
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AN 2001:6962873 INSPEC DN A2001-15-8140N-033
 TI The influence of crack-like defects on the tensile strength of an open-cell aluminum foam.
 AU Andrews, E.W.; Gibson, L.J. (Dept. of Mater. Sci. & Eng., MIT, Cambridge, MA, USA)
 SO Scripta Materialia (17 April 2001) vol.44, no.7, p.1005-10. 6 refs.
 Doc. No.: S1359-6462(01)00673-X
 Published by: Elsevier for Board of Directors of Acta Metall
 Price: CCCC 1359-6462/2001/\$20.00
 CODEN: SCRMBU ISSN: 1359-6462
 SICI: 1359-6462(20010417)44:7L.1005:ICLD;1-G
 DT Journal
 TC Experimental
 CY United States
 LA English

L8 ANSWER 4 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Link References
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AN 1997:5587190 INSPEC DN A9713-6848-002; B9707-2530F-005
 TI Effective KOH etching prior to modified Secco etching for **analyzing defects** in thin bonded silicon on insulator (SOI) wafers.
 AU Mitani, K.; Aga, H.; Nakano, M. (Isobe R&D Center, Gunma, Japan)
 SO Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers) (March 1997) vol.36, no.3B, p.1646-9. 10 refs.
 Published by: Publication Office, Japanese Journal Appl. Phys
 CODEN: JAPNDE ISSN: 0021-4922
 SICI: 0021-4922(199703)36:3BL.1646:EEPM;1-K
 Conference: 1996 International Conference on Solid State Devices and Materials (SSDM'96). Yokohama, Japan, 26-29 Aug 1996
 DT Conference Article; Journal
 TC Experimental
 CY Japan

LA English

L8 ANSWER 5 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Original References
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AN 1994:4825581 INSPEC DN A9501-6170-001
 TI Modeling the energy of formation of defects of various dimensionalities in crystals of intermetallic compounds.
 AU Starostenkov, M.D.; Dmitriev, S.V.; German, V.G. (Polzunov Altai State Univ., Barnaul, Russia)
 SO Crystallography Reports (Sept.-Oct. 1994) vol.39, no.5, p.720-4. 6 refs.
 Price: CCCC 1063-7745/94/3905-0720\$10.00
 CODEN: CYSTE3 ISSN: 1063-7745
 Translation of: Kristallografiya (Sept.-Oct. 1994) vol.39, no.5, p.798-802. 6 refs.
 CODEN: KRISAJ ISSN: 0023-4761
 DT Journal; Translation Abstracted
 TC Theoretical
 CY Russian Federation; Russian Federation
 LA English

L8 ANSWER 6 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Original References
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AN 1993:4454228 INSPEC DN B9309-4360-005
 TI Digital laser microscope for real-time defect imaging and review.
 AU Worster, B.W. (Ultrapointe Corp., Santa Clara, CA, USA); Politzer, B.A.
 SO Solid State Technology (May 1993) vol.36, no.5, p.55-6, 59. 2 refs.
 CODEN: SSTEAP ISSN: 0038-111X
 DT Journal
 TC Application; Practical
 CY United States
 LA English

L8 ANSWER 7 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Original References
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AN 1990:3720088 INSPEC DN B90060830
 TI Technique for failure analysis of tantalum capacitors.
 AU Macdonald, M.A.; Brindel, F.; Sousa, D. (Sprague Electr. Co., Sanford, ME, USA)
 SO 10th Capacitor and Resistor Technology Symposium. CARTS '90
 Huntsville, AL, USA: Components Technol. Inst, 1990. p.29-34 of 208 pp. 3 refs.
 Conference: San Francisco, CA, USA, 26-29 March 1990
 Sponsor(s): Components Technol. Inst.; IEEE
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L8 ANSWER 8 OF 8 INSPEC (C) 2005 IEE on STN

Full Text	Original References
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AN 1990:3681141 INSPEC DN B90052141; C90051710
 TI Algorithm for comparing fragments of images of two crystals for monitoring integrated circuit appearance.
 AU Ivanov, V.A.; Kosykh, V.P.
 SO Optoelectronics, Instrumentation and Data Processing (1989) no.2, p.29-34. 8 refs.

Price: CCCC 8756-6990/89/\$20.00
 CODEN: OIDPE4 ISSN: 8756-6990
 Translation of: Avtometriya (1989) no.2, p.29-34. 8 refs.
 CODEN: AVMEBI ISSN: 0320-7102
 DT Journal; Translation Abstracted
 TC Application; Practical
 CY USSR; United States
 LA English

=> s d-defects

296296 D

116900 DEFECTS

L9 85 D-DEFECTS
 (D(W) DEFECTS)

=> s 11 and 19

L10 7 L1 AND L9

=> d 110 1-7

L10 ANSWER 1 OF 7 INSPEC (C) 2005 IEE on STN

Full Text	Strike References
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AN 1998:6068361 INSPEC DN A9823-8110F-013; B9812-0510-026
 TI D-defects and metal-related flow patterns.
 AU Kissinger, G.; Morgenstern, G.; Richter, H. (Inst. fur Semicond. Phys., Frankfurt, Germany); Vanhellemont, J.; Graf, D.; Lambert, U.; Von Ammon, W.; Wagner, P.
 SO Proceedings of the Symposium on Crystalline Defects and Contamination: Their Impact and Control in Device Manufacturing II
 Editor(s): Kolbesen, B.O.; Claeys, C.; Stallhofer, P.; Tardiff, F.
 Pennington, NJ, USA: Electrochem. Soc, 1997. p.32-9 of x+518 pp. 13 refs.
 Conference: Paris, France, 31 Aug-5 Sept 1997
 ISBN: 1-56677-175-7
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L10 ANSWER 2 OF 7 INSPEC (C) 2005 IEE on STN

Full Text	Strike References
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AN 1992:4065619 INSPEC DN A9204-6170B-002
 TI Identification of vacancy clusters in FZ-Si crystals.
 AU Kitano, T. (VLSI Dev. Div., NEC Corp., Kanagawa, Japan)
 SO Physica Status Solidi A (16 Oct. 1991) vol.127, no.2, p.341-7. 16 refs.
 CODEN: PSSABA ISSN: 0031-8965
 DT Journal
 TC Experimental
 CY Germany, Federal Republic of
 LA English

L10 ANSWER 3 OF 7 INSPEC (C) 2005 IEE on STN

Full Text	Strike References
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AN 1991:3945455 INSPEC DN A91104121
 TI Behavior of point defects in FZ silicon crystals.
 AU Abe, T.; Kimura, M. (Isobe R&D Center, Gunma, Japan)
 SO Proceedings of the Sixth International Symposium on Silicon Materials

Science and Technology: Semiconductor Silicon 1990

Editor(s): Huff, H.R.; Barraclough, K.G.; Chikawa, J.-I.

Pennington, NJ, USA: Electrochem. Soc, 1990. p.105-16 of xix+1090 pp. 23 refs.

Conference: Montreal, Que., Canada, 7-11 May 1990

Sponsor(s): Electrochem. Soc

DT Conference Article

TC Experimental

CY United States

LA English

L10 ANSWER 4 OF 7 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1988:3115574 INSPEC DN A88054503

TI Investigation of **D defects** in silicon by X-ray topography.

AU Vysotskaya, V.V.; Gorin, S.N.; Sorokin, L.M.; Sheikhet, E.G. (A.A. Baikov Inst. of Metall., Acad. of Sci., Moscow, USSR)

SO Soviet Physics - Solid State (June 1987) vol.29, no.6, p.1068-70. 13 refs.
Price: CCCC 0038-5654/87/061068-03\$03.90

CODEN: SPSSA7 ISSN: 0038-5654

Translation of: Fizika Tverdogo Tela (June 1987) vol.29, no.6, p.1858-61. 13 refs.

CODEN: FTVTAC ISSN: 0367-3294

DT Journal; Translation Abstracted

TC Experimental

CY USSR; United States

LA English

L10 ANSWER 5 OF 7 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1987:2832599 INSPEC DN A87032340

TI Impurity effect on formation of microdefects during silicon crystal growth.

AU Chikawa, J. (Nat. Lab. for High Energy Phys., Tsukuba, Japan)

SO Proceedings of the Fifth International Symposium on Silicon Materials
Science and Technology: Semiconductor Silicon 1986

Editor(s): Huff, H.R.; Abe, T.; Kolbesen, B.

Pennington, NJ, USA: Electrochem. Soc, 1986. p.61-75 of xiv+1096 pp. 27 refs.

Conference: Boston, MA, USA, 5-9 May 1986

Sponsor(s): Electrochem. Soc

DT Conference Article

TC Experimental

CY United States

LA English

L10 ANSWER 6 OF 7 INSPEC (C) 2005 IEE on STN

Full Text	Links References
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AN 1983:2139319 INSPEC DN A83113905

TI Microdefects and impurities in dislocation-free silicon crystals.

AU Abe, T.; Harada, H. (Shin-Etsu Handotai Co., Gunma-ken, Japan); Chikawa, J.

SO Defects in Semiconductors II, Symposium Proceedings

Editor(s): Mahajan, S.; Corbett, J.W.

New York, NY, USA: North-Holland, 1983. p.1-17 of xv+582 pp. 26 refs.

Conference: Boston, MA, USA, Nov 1982

ISBN: 0-444-00812-8

DT Conference Article
 TC Experimental
 CY United States
 LA English

L10 ANSWER 7 OF 7 INSPEC (C) 2005 IEE on STN



AN 1983:2039012 INSPEC DN A83046938
 TI Swirl defects in float-zoned silicon crystals.
 AU Abe, T. (Shin-Etsu Handotai Co., Gunma-ken, Japan); Harada, H.; Chikawa, J.
 SO Physica B & C (Feb. 1983) vol.116B+C, no.1-3, p.139-47. 28 refs.
 Price: CCCC 0378-4363/83/0000-0000/\$03.00
 CODEN: PHBCDQ ISSN: 0378-4363
 Conference: Proceedings of the 12th International Conference on Defects in Semiconductors. Amsterdam, Netherlands, 31 Aug-3 Sept 1982
 Sponsor(s): IUPAP; European Phys. Soc.; Netherlands' Phys. Soc.; Univ. Amsterdam
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

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